



20V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
-20V	$5.5 \text{m}\Omega$ @ $V_{GS} = -4.5V$	-40A
	$7.5 \text{m}\Omega$ @ $V_{GS} = -2.5 \text{V}$	-40A

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

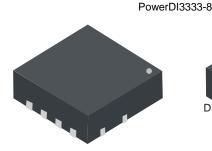
- Load Switch
- Power Management Functions

Features

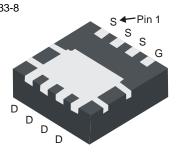
- Low R_{DS(ON)} Ensures On State Losses are Minimized
- Small Form Factor, Thermally Efficient Package Enables Higher Density End Products
- Occupies just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

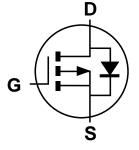
Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.030 grams (Approximate)



Top View





Bottom View

Equivalent Circuit

Ordering Information (Note 5)

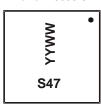
Part Number	Case	Packaging
DMP2006UFGQ-7	PowerDI3333-8	2,000/Tape & Reel
DMP2006UFGQ-13	PowerDI3333-8	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information

PowerDI3333-8



S47 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 17 = 2017) WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	-20	V		
Gate-Source Voltage			V_{GSS}	±10	V
Continuous Drain Current (Note 6) V_{GS} = -4.5V Steady State $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$ $T_C = +25^{\circ}C$		I _D	-17.5 -14.0 -40	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-80	А		
Maximum Continuous Body Diode Forward Current (Note 6)			Is	-2.2	Α
Avalanche Current (Note 8) L = 0.1mH			I _{AS}	-23	Α
Avalanche Energy (Note 8) L = 0.1mH	E _{AS}	28	mJ		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 6)	$T_A = +25$ °C	ם	2.3	- W
Total Power Dissipation (Note 6)	$T_C = +25$ °C	P_{D}	41	
Thermal Resistance, Junction to Ambient	(Note 5)	D	54	
Themal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	136	°C/W
Thermal Resistance, Junction to Case (Note 6)	$R_{ heta JC}$	3.0		
Operating and Storage Temperature Range	$T_{J_{i}}T_{STG}$	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_		-1	μA	V _{DS} = -16V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_		±100	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	-0.4		-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
		_	4.2	5.5	mΩ	$V_{GS} = -4.5V, I_D = -15A$	
Static Drain-Source On-Resistance	D	_	5.4	7.5		$V_{GS} = -2.5V, I_D = -10A$	
Static Diani-Source On-Resistance	R _{DS(ON)}	_	8	12	11112	$V_{GS} = -1.8V, I_D = -1A$	
		_	12	17		$V_{GS} = -1.5V, I_D = -1A$	
Diode Forward Voltage	V_{SD}	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -10A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	_	5404	7500		$V_{DS} = -10V, V_{GS} = 0V$ f = 1.0MHz	
Output Capacitance	Coss	_	728	1000	pF		
Reverse Transfer Capacitance	C _{rss}	_	612	900			
Gate Resistance	Rg	_	3.8	8	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Q_{g}	_	64	100			
Total Gate Charge (V _{GS} = -10V)	Qg	_	140	200	nC	V _{DD} = -10V. I _D = -20A	
Gate-Source Charge	Q_{gs}	_	8.5	15	IIC	$V_{DD} = -10V, I_{D} = -20A$	
Gate-Drain Charge	Q _{gd}	_	17	30			
Turn-On Delay Time	t _{D(ON)}	_	9.1	20			
Turn-On Rise Time	t _R	_	19	35		$V_{GS} = -4.5V, V_{DD} = -10V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	146	220	ns	$R_g = 1\Omega$, $I_D = -10A$	
Turn-Off Fall Time	t _F	_	104	150			
Reverse Recovery Time (Note 9)	t _{RR}	_	61	100	ns	I _F = -10A, di/dt = 100A/μs	
Reverse Recovery Charge (Note 9)	Q _{RR}		44	70	nC	I _F = -10A, di/dt = 100A/µs	

Notes: 6. R_{0JA} is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. R_{0JC} is guaranteed by design while R_{0JA} is determined by the user's board design.

^{7.} Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

^{8 .}UIS in production with L = 0.1 mH, $T_J = +25 ^{\circ}\text{C}$.

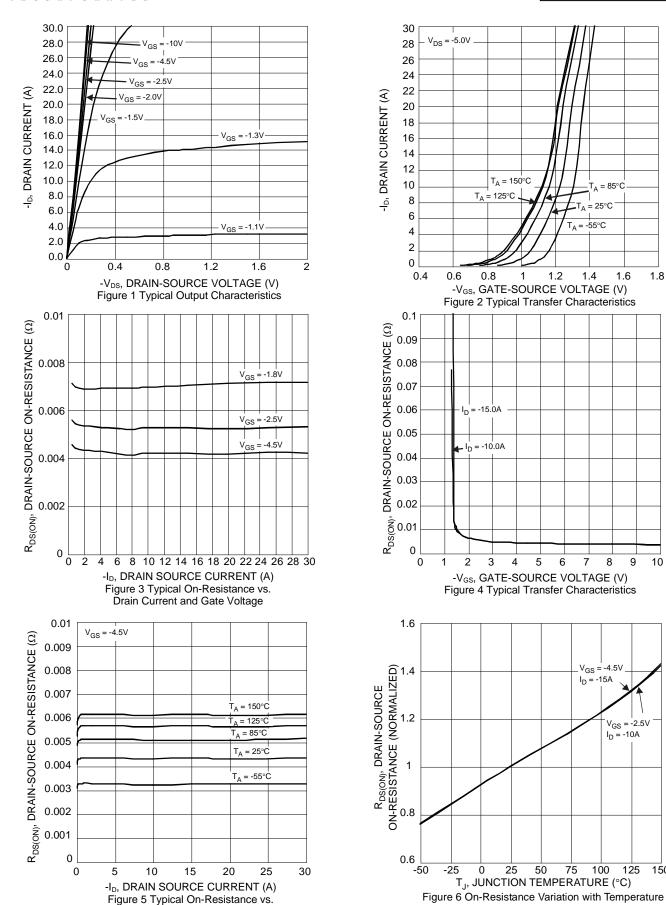
^{9.} Short duration pulse test used to minimize self-heating effect.

^{10.} Guaranteed by design. Not subject to product testing.

1.8

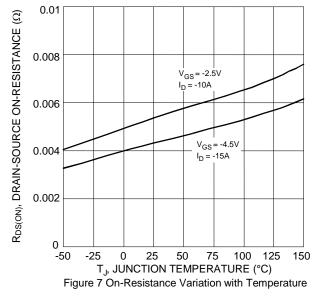
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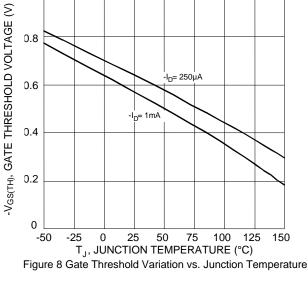




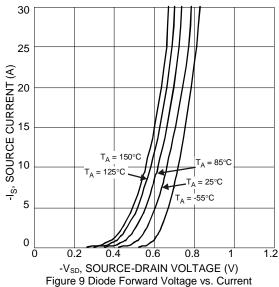
Drain Current and Temperature

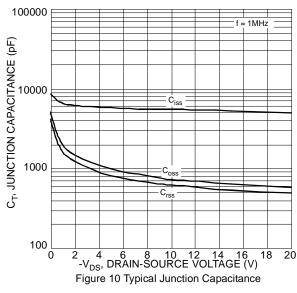


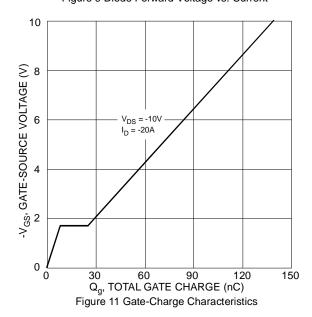


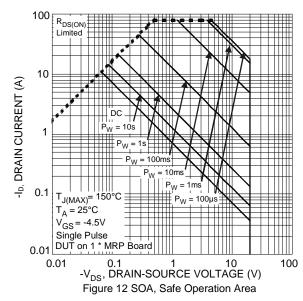


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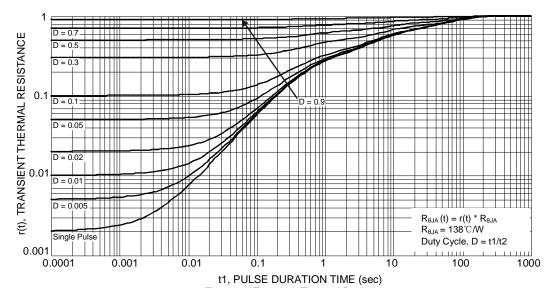


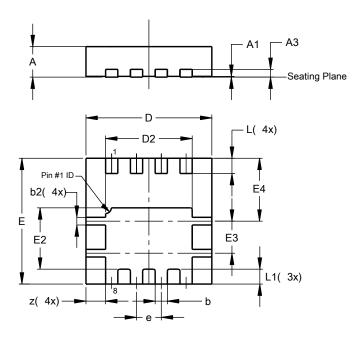
Figure 13 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8

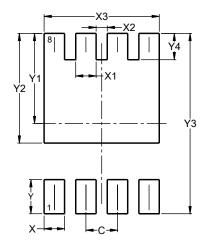


PowerDI3333-8					
Dim	Min Max		Тур		
Α	0.75	0.85	0.80		
A 1	0.00	0.05	0.02		
A3	_	_	0.203		
b	0.27	0.37	0.32		
b2	0.15	0.25	0.20		
D	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
Е	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
E3	0.79	0.89	0.84		
E4	1.60	1.70	1.65		
е	-	_	0.65		
L	0.35	0.45	0.40		
L1	_	_	0.39		
Z	_	_	0.515		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
С	0.650
X	0.420
X1	0.420
X2	0.230
Х3	2.370
Υ	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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